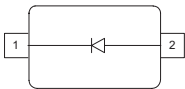


Silicon Schottky Diode

- High current rectifier Schottky diode with extreme low V_F drop (typ. 0.12V at $I_F = 10\text{mA}$)
- For power supply applications
- For clamping and protection in low voltage applications
- For detection and step-up-conversion



BAT60A



ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Package	Configuration	Marking
BAT60A	SOD323	single	white/3

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	10	V
Forward current	I_F	3	A
Surge forward current, ($t \leq 10\text{ms}$)	I_{FSM}	5	
Total power dissipation $T_S \leq 28^\circ\text{C}$	P_{tot}	1350	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 90	K/W

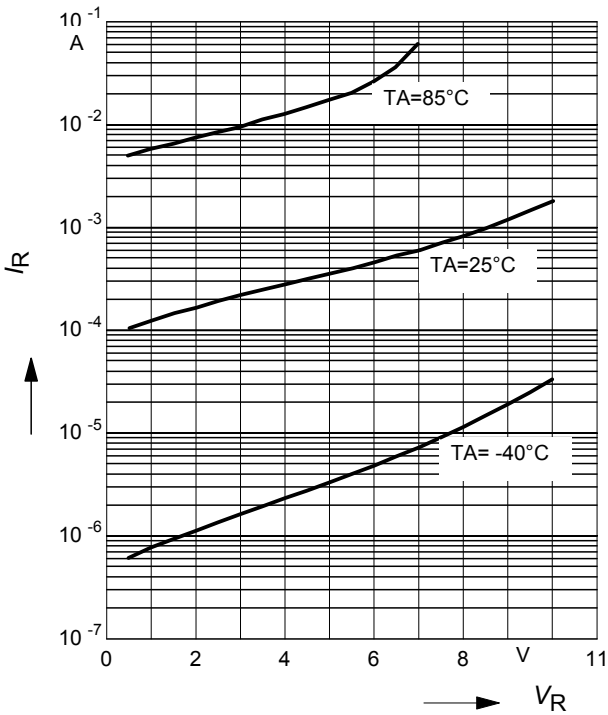
¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current	I_R				mA
$V_R = 5\text{ V}$		-	0.3	1	
$V_R = 8\text{ V}$		-	0.6	2.6	
$V_R = 5\text{ V}, T_A = 80^\circ\text{C}$		-	18	-	
Forward voltage	V_F				V
$I_F = 10\text{ mA}$		0.1	0.12	0.15	
$I_F = 100\text{ mA}$		0.15	0.2	0.23	
$I_F = 1000\text{ mA}$		0.22	0.3	0.37	
AC Characteristics					
Diode capacitance	C_T	-	20	35	pF
$V_R = 5\text{ V}, f = 1\text{ MHz}$					

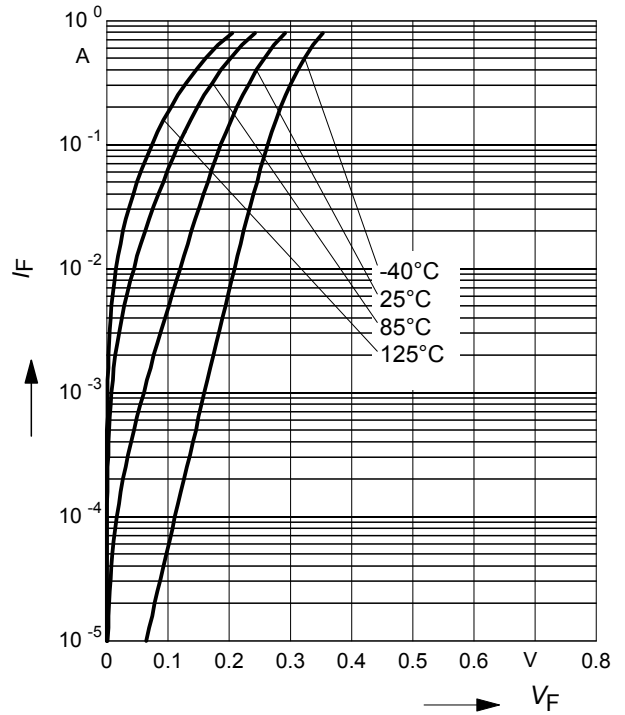
Reverse current $I_R = f(V_R)$

$T_A = \text{Parameter}$

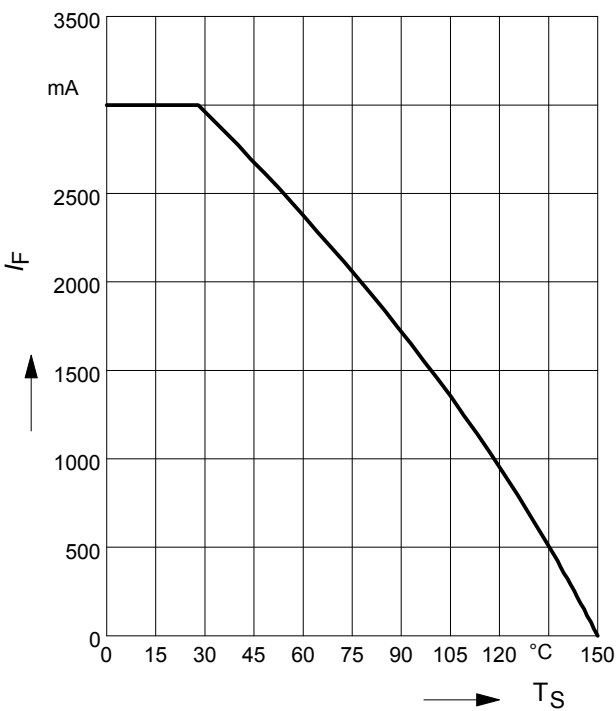


Forward current $I_F = f(V_F)$

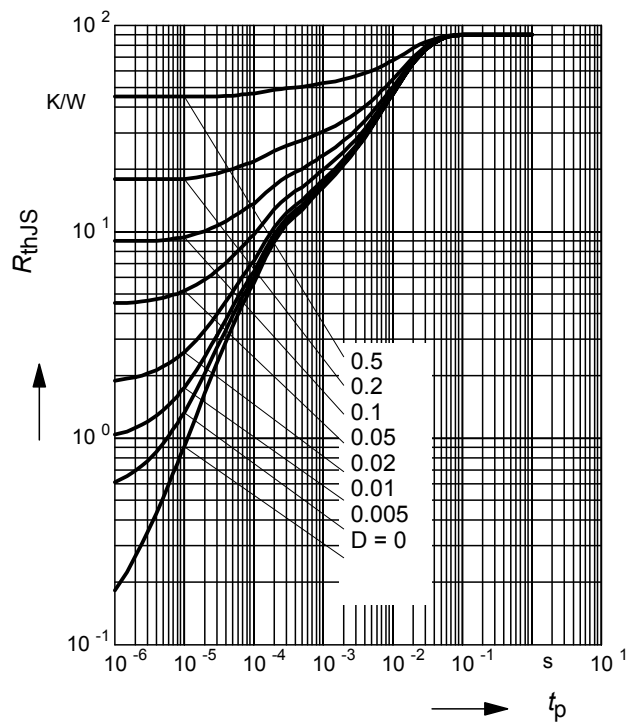
$T_A = \text{Parameter}$



Forward current $I_F = f(T_S)$

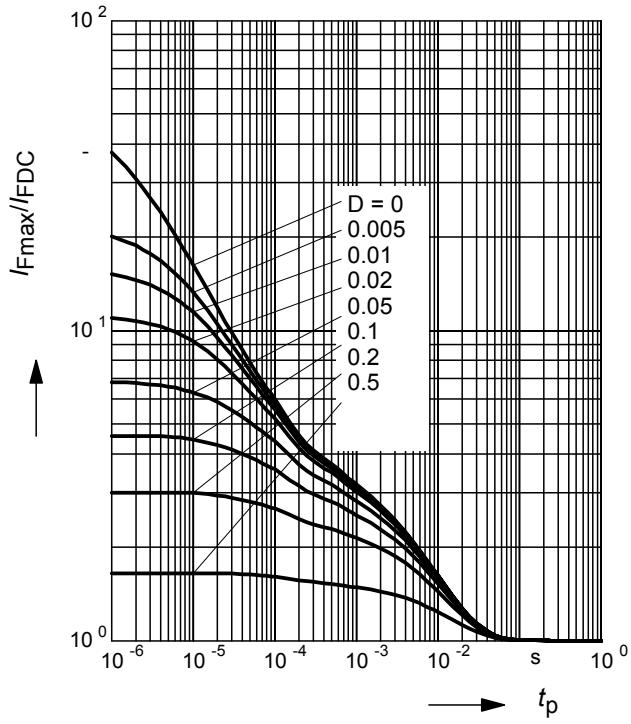


Permissible Puls Load $R_{thJS} = f(t_p)$



Permissible Pulse Load

$$I_{Fmax} / I_{FDC} = f(t_p)$$



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Datasheets for electronics components.